



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

- V_{DS} 100V
- I_D 130A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) $< 5.5m\Omega$
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) $< 6.5m\Omega$
- 100% UIS Tested
- 100% ∇V_{DS} Tested

General Description

- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- Power switching application
- Uninterruptible power supply
- DC-DC



YJP130G10A

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	1	μA
		V _{DS} =100V, V _{GS} =0V, T _J =150°C	-	-	100	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1	1.8	2.5	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =65A	-	4	5.5	mΩ
		V _{GS} =10V, I _D =20A	-	4	5.5	
		V _{GS} =4.5V, I _D =20A	-	5	6.5	
Diode Forward Voltage	V _{SD}	I _S =65A, V _{GS} =0V	-	0.9	1.2	V
Gate resistance	R _G	f=1MHz, Open drain	-	0.8	-	Ω
Maximum Body-Diode Continuous Current	I _S		-	-	130	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, f=1MHz	-	4450	-	pF
Output Capacitance	C _{oss}		-	1500	-	
Reverse Transfer Capacitance	C _{rss}		-	90	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =50V, I _D =65A	-	68	-	nC
Gate-Source Charge	Q _{gs}		-	11	-	
Gate-Drain Charge	Q _{gd}		-	16	-	
Reverse Recovery Charge	Q _{rr}	I _F =65A, di/dt=600A/us	-	160	-	nC
Reverse Recovery Time	t _{rr}		-	35	-	ns
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DD} =50V, I _D =65A R _{GEN} =2.2Ω	-	18	-	ns
Turn-on Rise Time	t _r		-	79	-	
Turn-off Delay Time	t _{D(off)}		-	33	-	
Turn-off fall Time	t _f		-	7	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. T_J=25°C, V_{DD}=50V, V_G=10V, R_G=25Ω, L=0.5mH, I_{AS}=37A.

C. P_g is based on max. junction temperature, using junction-case thermal resistance.

D. The value of R_{θJA} is measured with the device mounted on the minimum recommend pad size, in the still air environment with T_A=25°C. The maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.



YJP130G10A

Typical Electrical and Thermal Characteristics Diagrams

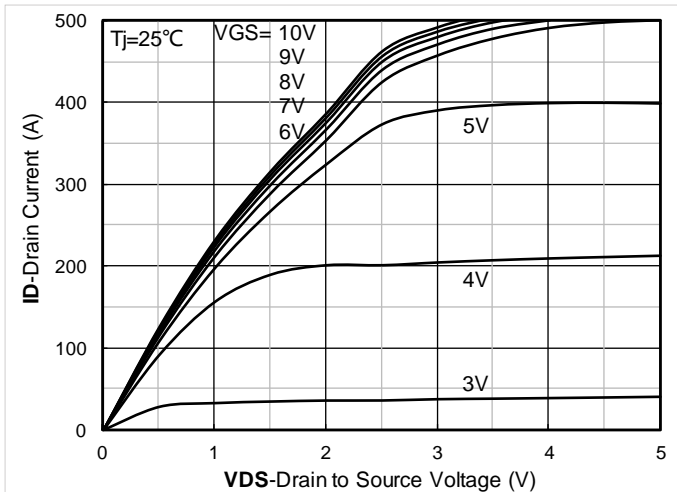


Figure 1. Output Characteristics

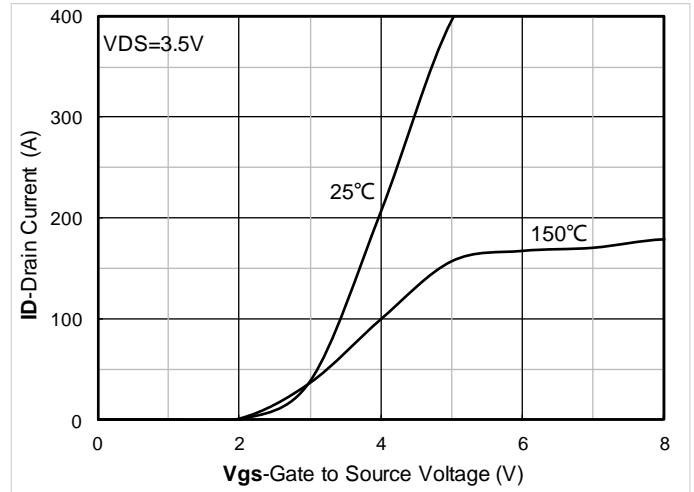


Figure 2. Transfer Characteristics

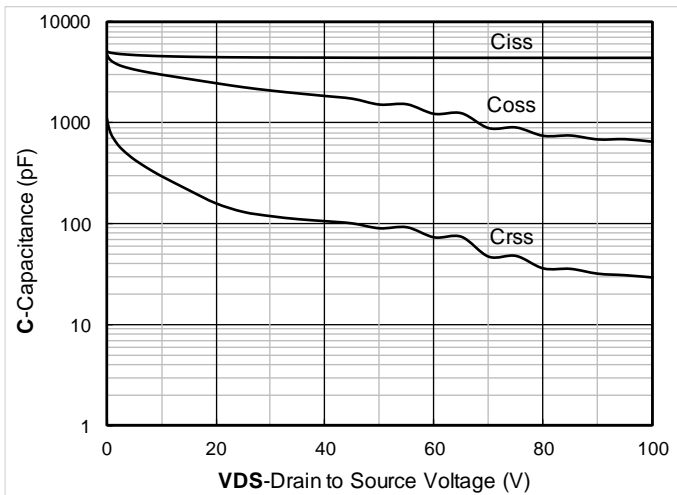


Figure 3. Capacitance Characteristics

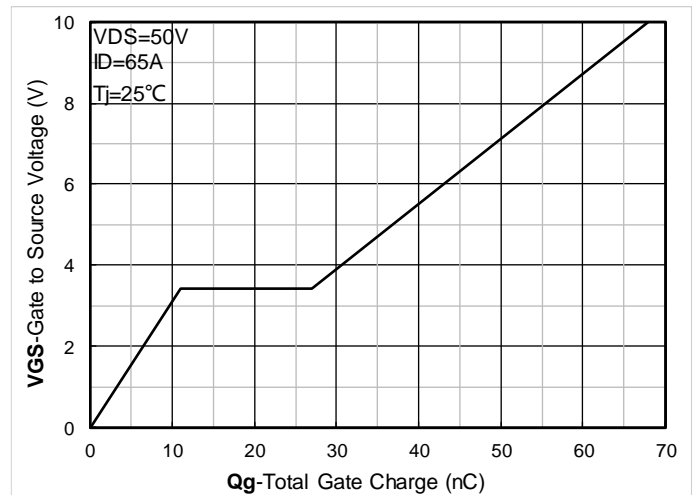


Figure 4. Gate Charge

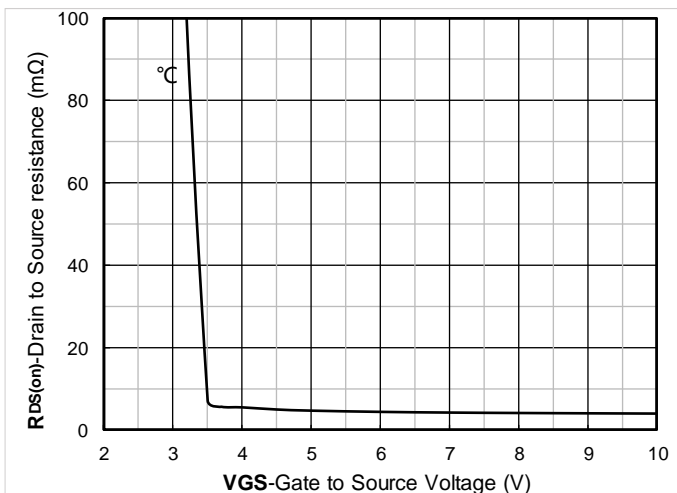


Figure 5. On-Resistance vs Gate to Source Voltage

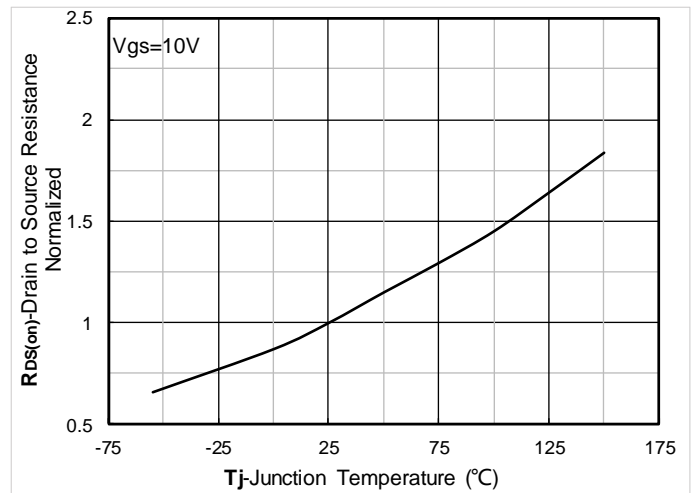


Figure 6. Normalized On-Resistance



YJP130G10A

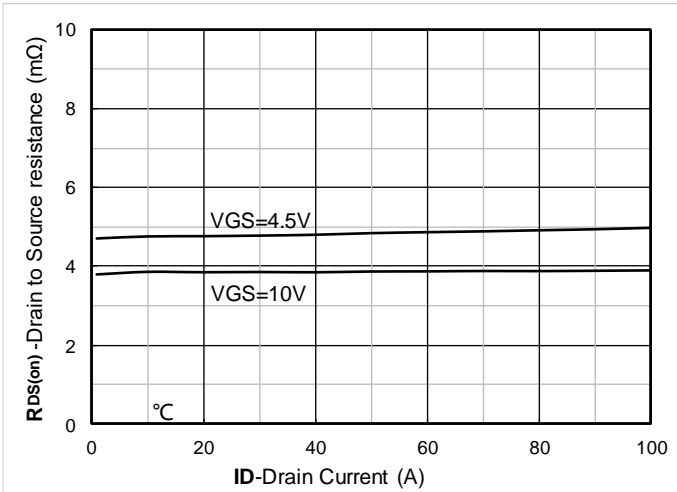


Figure 7. RDS(on) VS Drain Current

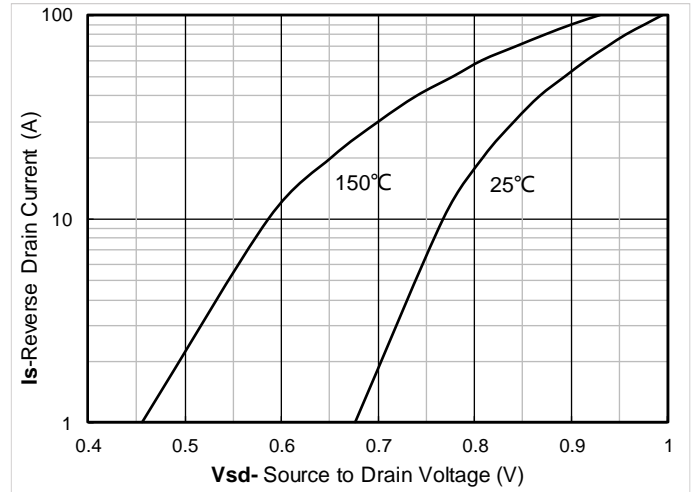


Figure 8. Forward characteristics of reverse diode

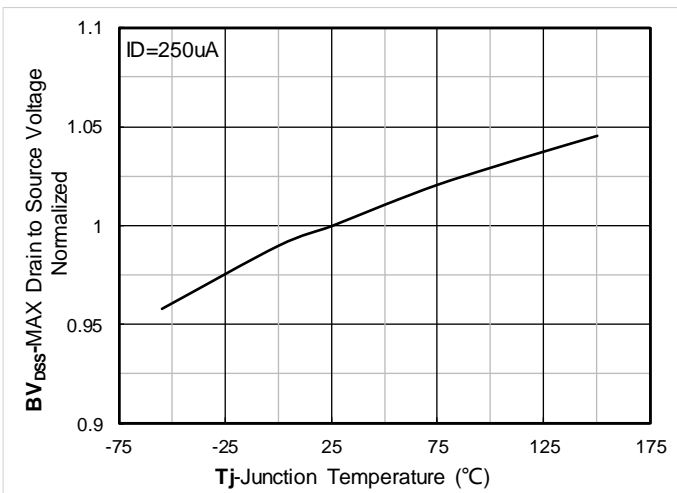


Figure 9. Normalized breakdown voltage

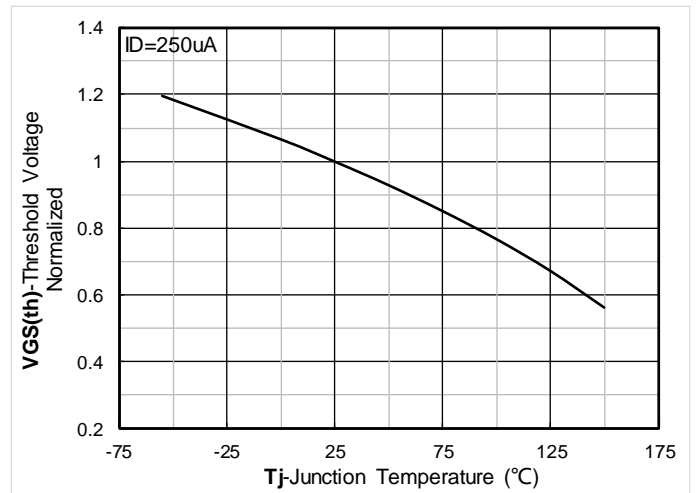


Figure 10. Normalized Threshold voltage

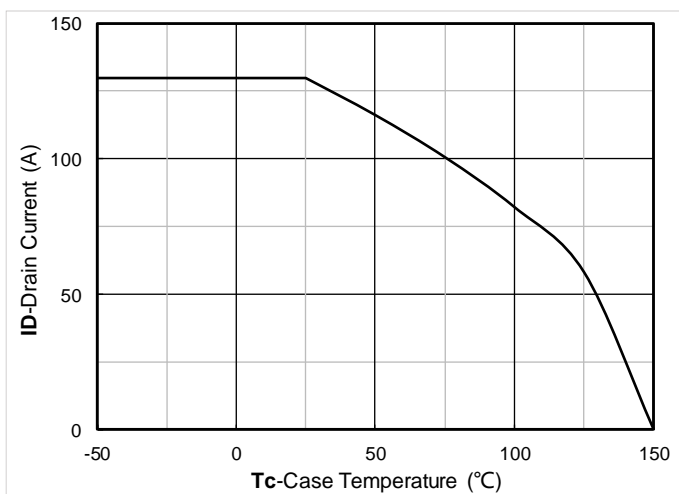


Figure 11. Current dissipation

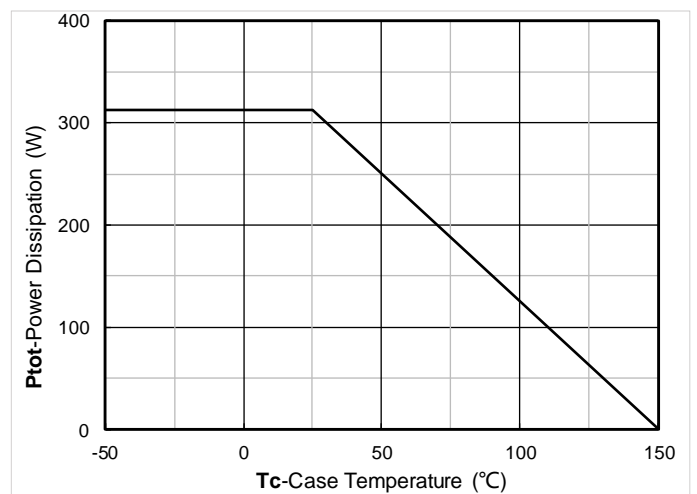


Figure 12. Power dissipation

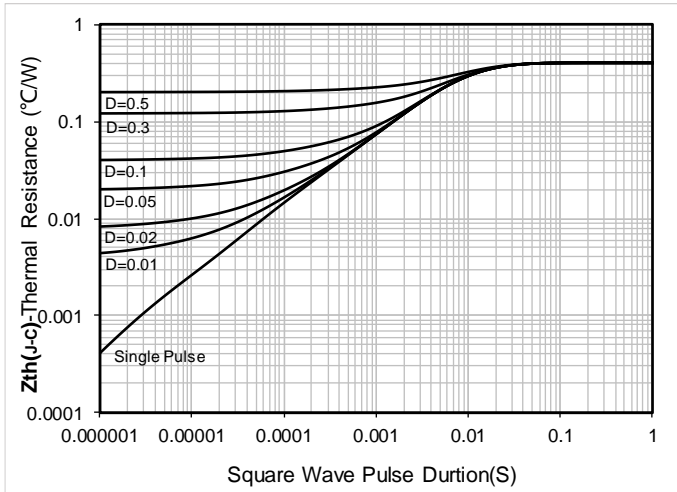


Figure 13. Maximum Transient Thermal Impedance

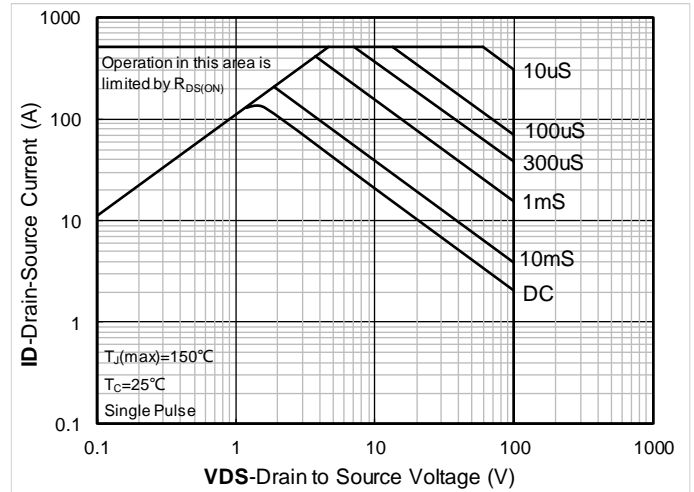


Figure 14. Safe Operation Area

■ Test Circuits & Waveforms

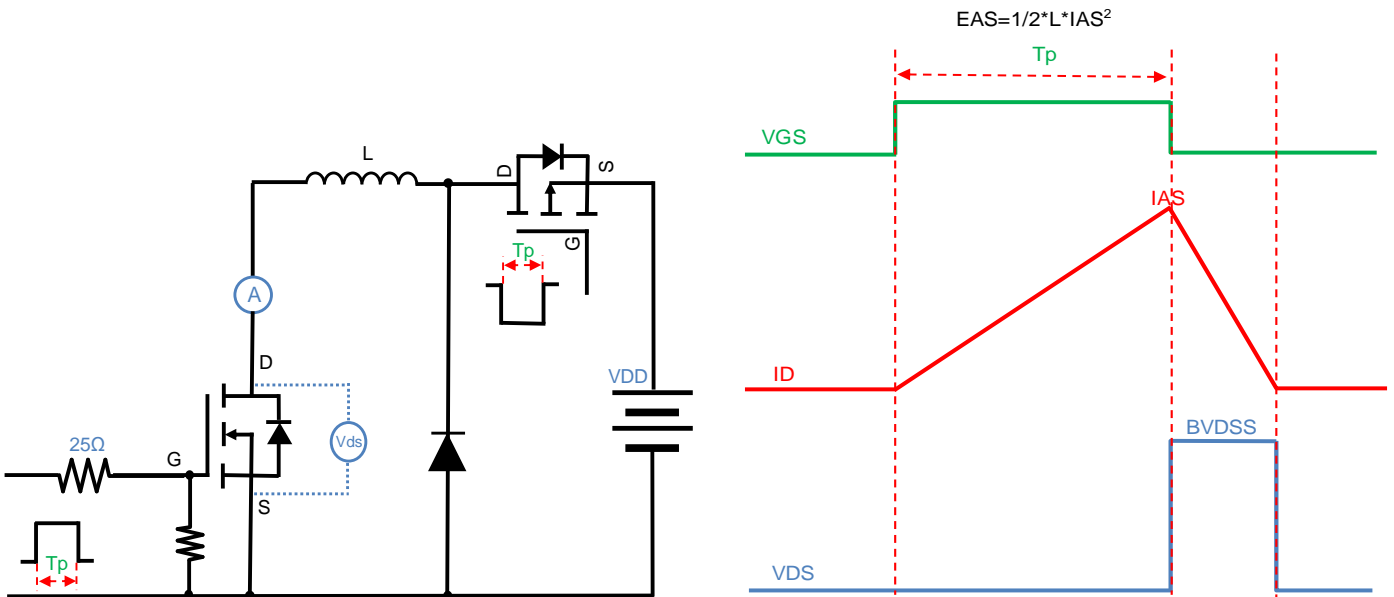


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

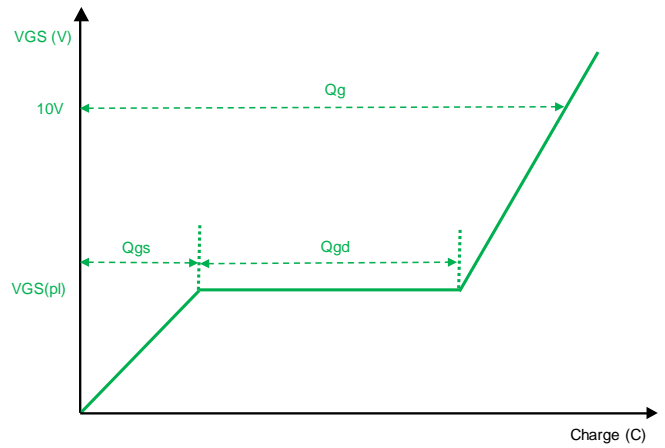
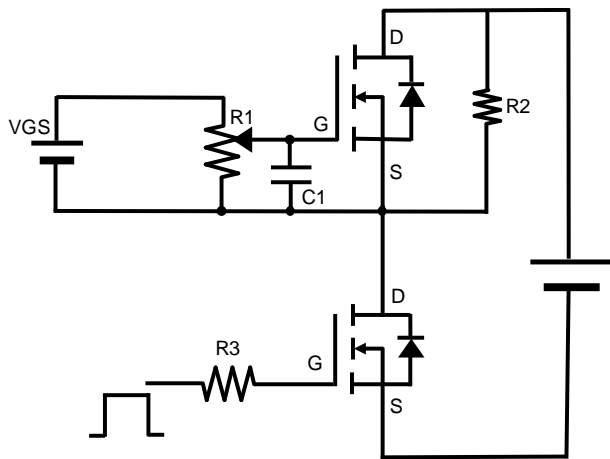


Figure B. Gate Charge Test Circuit & Waveform

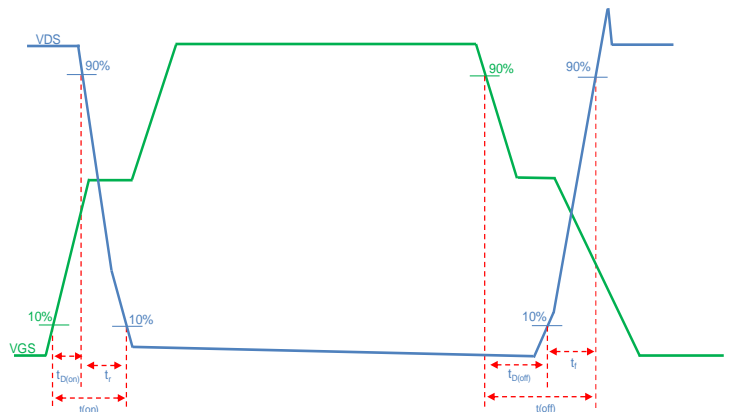
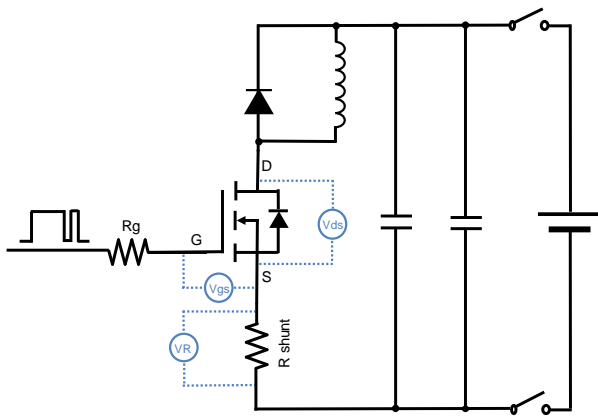


Figure C. Resistive Switching Test Circuit & Waveform

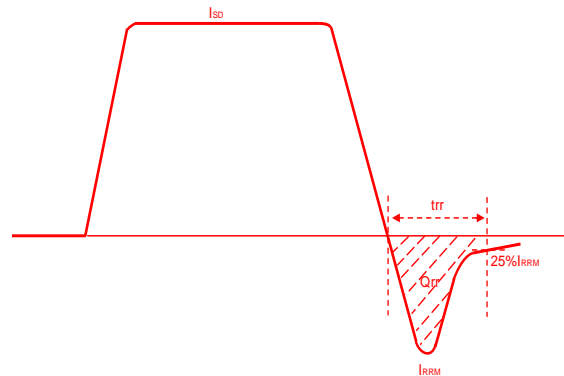
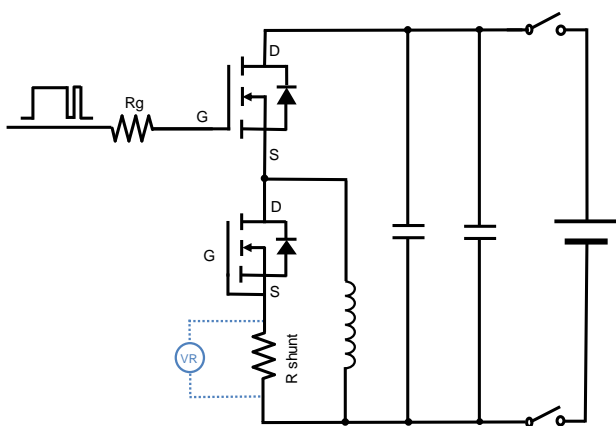
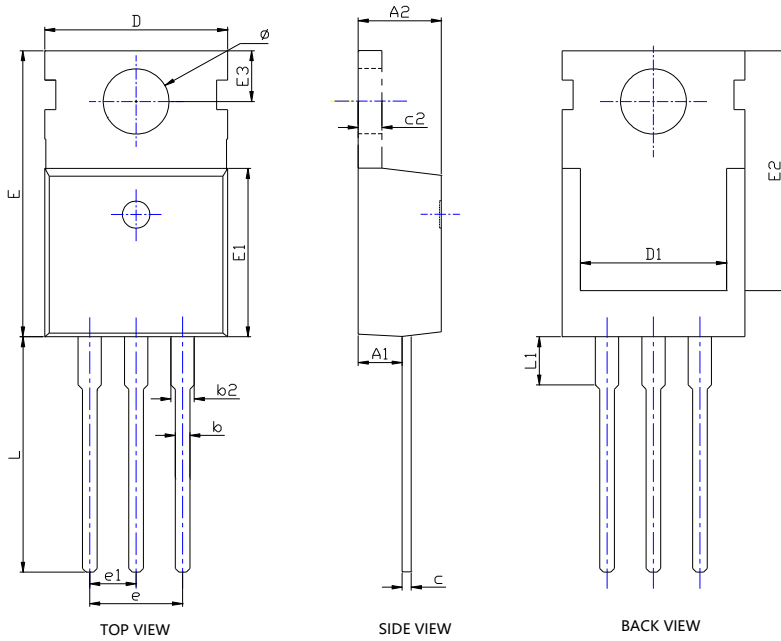


Figure D. Diode Recovery Test Circuit & Waveform



YJP130G10A

■ TO-220AB-D Package information



SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A1	0.091	0.098	2.300	2.500
A2	0.175	0.183	4.450	4.650
b	0.030	0.033	0.750	0.850
b2	0.048	0.052	1.220	1.320
c	0.018	0.022	0.450	0.550
c2	0.050	0.052	1.270	1.330
D	0.386	0.402	9.800	10.200
D1	0.303	0.327	7.700	8.300
E	0.614	0.630	15.600	16.000
E1	0.360	0.372	9.150	9.450
E2	0.510	0.533	12.950	13.550
E3	0.110BSC		2.800BSC	
e	0.200BSC		5.080BSC	
e1	0.100BSC		2.540BSC	
L	0.506	0.518	12.850	13.150
L1	0.093	0.117	2.360	2.960
ϕ	0.138	0.146	3.500	3.700

NOTE:
 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
 2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.



YJP130G10A

Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website <http://www.21yangjie.com> , or consult your nearest Yangjie's sales office for further assistance.